

CLAIMS:

1. A method for the manufacture of a display comprising
 - providing a substrate
 - depositing a removable layer to said substrate covering at least a part of said substrate,
- 5 characterized in
 - depositing an etch and temperature resistant layer on said removable layer, essentially covering said removable layer,
 - processing a display on at least part of said etch and temperature resistant layer, and
- 10 - removing said removable layer by etching with an etchant, said etch and temperature resistant layer preventing the etchant from making contact with said display.
2. A method according to claim 1, wherein said substrate is provided with etch openings and said etching is performed by leading an etchant through the substrate through
- 15 said etch openings.
3. A method according to claim 1 or 2, wherein said substrate comprises a silicon material.
- 20 4. A method according to claim 4, wherein said substrate comprises polysilicon plates.
5. A method according to claim 4, wherein said substrate comprises silicon microsieves.
- 25 6. A method according to claim 4, wherein said substrate comprises a silicon wafer.

7. A method according to any one of the preceding claims, wherein said substrate has a height profile which can be passed on to the display.

8. A method according to any one of the preceding claims, wherein said etch and temperature resistant layer comprises Si_3N_4 .

9. A method according to any one of the preceding claims, wherein said etch and temperature resistant layer comprises stacks of Si_3N_4 and SiO_2 .

10. A method according to any one of the preceding claims, wherein said etch and temperature resistant layer comprises SiON .

11. A method according to any one of the preceding claims, wherein said etch and temperature resistant layer comprises stacks of Si_3N_4 and SiON .

12. A method according to any one of the preceding claims, wherein said etch and temperature resistant layer comprises stacks of stacks of SiO_2 and SiON .

13. A method according to any one of the preceding claims, wherein said etch and temperature resistant layer comprises stacks of Si_3N_4 , SiO_2 and SiON .

14. A method according to any one of the preceding, wherein said removable layer comprises SiO_2 .

15. A method according to any one of the preceding, wherein said etchant comprises a HF-solution.

16. A method according to any one of the preceding, wherein said etchant comprises $\text{NH}_4\text{F}:\text{HF}$.

17. A display obtainable using the method according to any one of the preceding claims.

18. A method according to any one of the preceding claims for non display applications, e.g. plastic electronics, MEMS, and Passive Integration.